



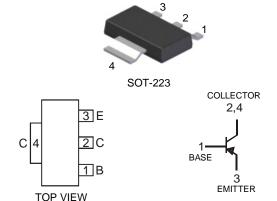
#### PNP SURFACE MOUNT TRANSISTOR

### **Features**

- **Epitaxial Planar Die Construction**
- Complementary NPN Type Available (DZT5551)
- Ideally Suited for Automated Assembly Processes
- Ideal for Medium Power Switching or Amplification Applications
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 3)

## **Mechanical Data**

- Case: SOT-223
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Finish Matte Tin annealed over Copper Leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Marking & Type Code Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.112 grams (approximate)



Schematic and Pin Configuration

## **Maximum Ratings** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	$V_{CBO}$	-160	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-150	V
Emitter-Base Voltage	V <sub>EBO</sub>	-5.0	V
Collector Current	I <sub>C</sub>	-600	mA

### **Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Power Dissipation @T <sub>A</sub> = 25°C (Note 3)	$P_{D}$	1	W
Thermal Resistance, Junction to Ambient @T <sub>A</sub> = 25°C (Note 3)	$R_{ hetaJA}$	125	°C/W
Operating and Storage Temperature Range	T <sub>j</sub> , T <sub>STG</sub>	-55 to +150	°C

## **Electrical Characteristics** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 4)					
Collector-Base Breakdown Voltage	V <sub>(BR)CBO</sub>	-160	_	V	$I_C = -100 \mu A, I_E = 0$
Collector-Emitter Breakdown Voltage	V <sub>(BR)CEO</sub>	-150	_	V	$I_C = -1.0 \text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	V <sub>(BR)EBO</sub>	-5.0	_	V	$I_E = -10\mu A, I_C = 0$
Collector Cutoff Current	1		-50	nA	$V_{CB} = -120V, I_{E} = 0$
Collector Cutoff Current	I <sub>CBO</sub>	_	-30	μΑ	$V_{CB} = -120V$ , $I_E = 0$ , $T_A = 150$ °C
Emitter Cutoff Current	I <sub>EBO</sub>	1	-50	nA	$V_{EB} = -3.0V, I_C = 0$
ON CHARACTERISTICS (Note 4)					
		50	_		$I_C = -1.0 \text{mA}, V_{CE} = -5.0 \text{V}$
DC Current Gain	h <sub>FE</sub>	60	240	_	$I_C = -10 \text{mA}, V_{CE} = -5.0 \text{V}$
		50			$I_C = -50 \text{mA}, V_{CE} = -5.0 \text{V}$
Collector-Emitter Saturation Voltage	\/		-0.2	V	$I_C = -10 \text{mA}, I_B = -1.0 \text{mA}$
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>		-0.5		$I_C = -50 \text{mA}, I_B = -5.0 \text{mA}$
Base-Emitter Saturation Voltage	V <sub>BE(SAT)</sub>		-1.0	V	$I_C = -10mA$ , $I_B = -1.0mA$
Dase-Emilier Saturation Voltage					$I_C = -50 \text{mA}, I_B = -5.0 \text{mA}$
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	$C_{obo}$	_	6.0	pF	$V_{CB} = -10V$ , $f = 1.0MHz$ , $I_E = 0$
Small Signal Current Gain	h <sub>fe</sub>	40	200	_	$V_{CE} = -10V$ , $I_{C} = -1.0$ mA, $f = 1.0$ kHz
Current Gain-Bandwidth Product	f <sub>T</sub>	100	300	MHz	V <sub>CE</sub> = -10V, I <sub>C</sub> = -10mA, f = 100MHz
Noise Figure	NF	_	8.0	dB	$V_{CE} = -5.0V$ , $I_{C} = -200\mu A$ , $R_{S} = 10\Omega$ , $f = 1.0kHz$

Notes:

- No purposefully added lead.
- Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead\_free/index.php.

  Device mounted on FR-4 PCB, pad layout as shown on page 4 or in Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.
- 4. Measured under pulsed conditions. Pulse width = 300ms. Duty cycle ≤ 2%.



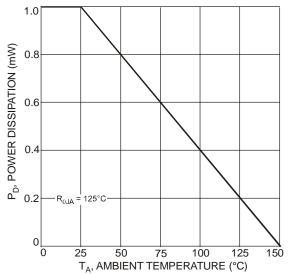


Fig. 1 Max Power Dissipation vs. Ambient Temperature

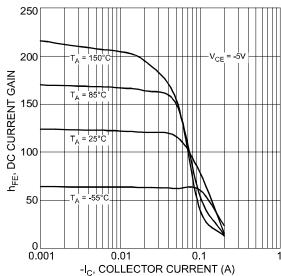


Fig. 3 Typical DC Current Gain vs. Collector Current

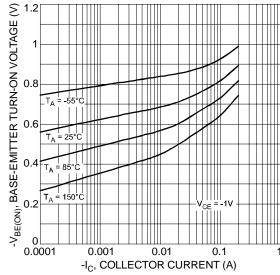


Fig. 5 Typical Base-Emitter Turn-On Voltage vs. Collector Current

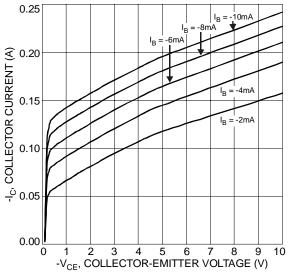


Fig. 2 Typical Collector Current vs. Collector-Emitter Voltage

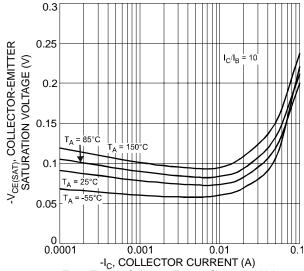


Fig. 4 Typical Collector-Emitter Saturation Voltage vs. Collector Current

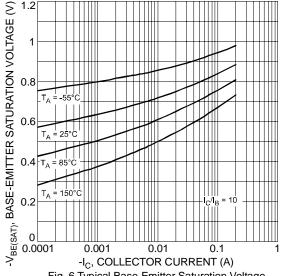
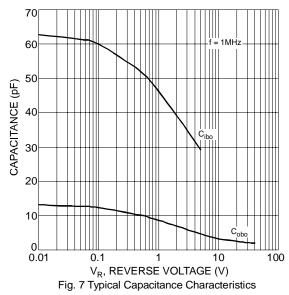


Fig. 6 Typical Base-Emitter Saturation Voltage vs. Collector Current





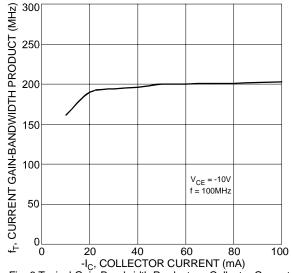


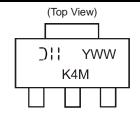
Fig. 8 Typical Gain-Bandwidth Product vs. Collector Current

## Ordering Information (Note 5)

Device	Packaging	Shipping	
DZT5401-13	SOT-223	2500/Tape & Reel	

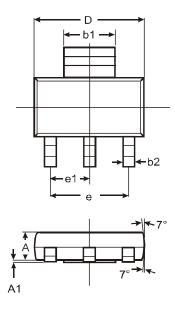
Notes: 5. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

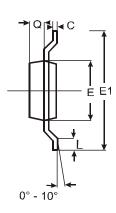
## **Marking Information**



K4M = Product type marking code
OH = Manufacturer's code marking
YWW = Date code marking
Y = Last digit of year ex: 7 = 2007
WW = Week code 01 - 52

# **Package Outline Dimensions**

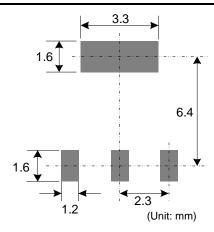




SOT-223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b1	2.90	3.10	3.00		
b2	0.60	0.80	0.70		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
Е	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	_		4.60		
e1			2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All Dimensions in mm					



## **Suggested Pad Layout**



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